



## PATENT ABSTRACTS OF JAPAN

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MANUFACTURE THEREOF**

transistor is used.

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(57) Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor device, which matches low production cost, low consumption power and high-speed and a method of manufacturing the device.

**SOLUTION:** A first transistor has a high threshold voltage by a heavily doped substrate region 15 and as a punch-through between source, and drain regions can be inhibited by a punch-through stopper layer 9, an off leakage current in the first transistor can be reduced and the first transistor is suited to low consumption power. In a second transistor, as the second transistor is provided with a lightly doped channel region 13b in the entire channel region, the second transistor has a low threshold voltage and has a high drive current. The junction capacitance between source and drain diffused layers 11 is reduced by a lightly doped substrate region 7 formed under the bottoms of the layers 11. At the one time of a power supply, the second transistor is used and at the off time of the power supply, the first

